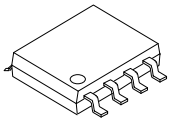
15A, 100V DUAL N-CHANNEL ENHANCEMENT MODE POWER MOSFET



SOP-8

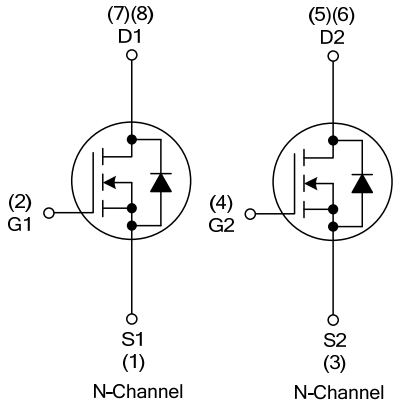
■ DESCRIPTION

The UTC **15NN10M** is a Dual N-channel enhancement mode power MOSFET using UTC's perfect technology to provide customers with fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

■ FEATURES

* $R_{DS(ON)} \leq 90\ m\Omega$ @ V_{GS}=10V, I_D=7.5A
* $R_{DS(ON)} \leq 100\ m\Omega$ @ V_{GS}=4.5V, I_D=7.5A
* High switching speed
* Low Gate Charge
* Simple Drive Requirement

■ SYMBOL



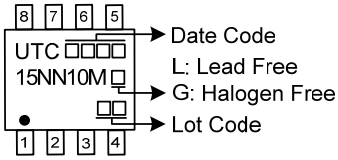
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment						Packing
Lead Free	Halogen Free		1	2	3	4	5, 6	7, 8	
15NN10ML-S08-R	15NN10MG-S08-R	SOP-8	S1	G1	S2	G2	D2	D1	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

15NN10MG-S08-R (1)Packing Type	(1) R: Tape Reel
(2)Package Type	(2) S08: SOP-8
(3)Green Package	(3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING


8 7 6 5
UTC □□□□
15NN10M □
□□
1 2 3 4
Date Code
L: Lead Free
G: Halogen Free
Lot Code

■ ABSOLUTE MAXIMUM RATING (T_C=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	100	V
Gate-Source Voltage		V_{GSS}	±20	V
Drain Current	DC	I_D	15	A
	Pulsed (Note 2)	I_{DM}	30	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	31.2	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	5	V/ns
Power Dissipation		P_D	4.2	W
Junction Temperature		T_J	+150	°C
Storage Temperature Range		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature.
3. L = 0.1mH, I_{AS} = 25A, V_{DD} = 50V, R_G = 25Ω, Starting T_J = 25°C.
4. I_{SD} ≤ 15A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J=25°C.

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	125	°C/W
Junction to Case	θ_{JC}	29.7	°C/W

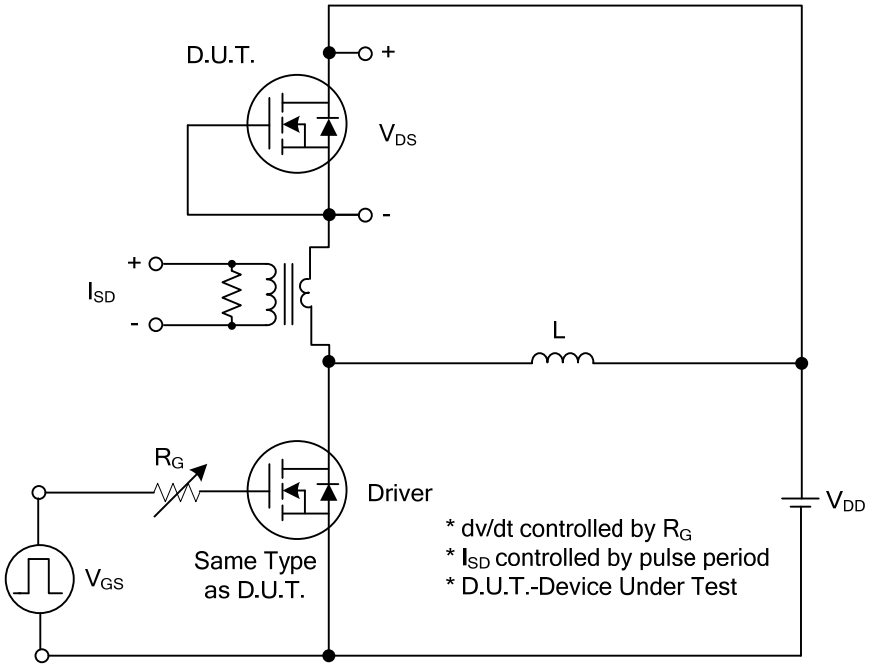
Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

■ ELECTRICAL CHARACTERISTICS (T_J=25°C unless otherwise specified)

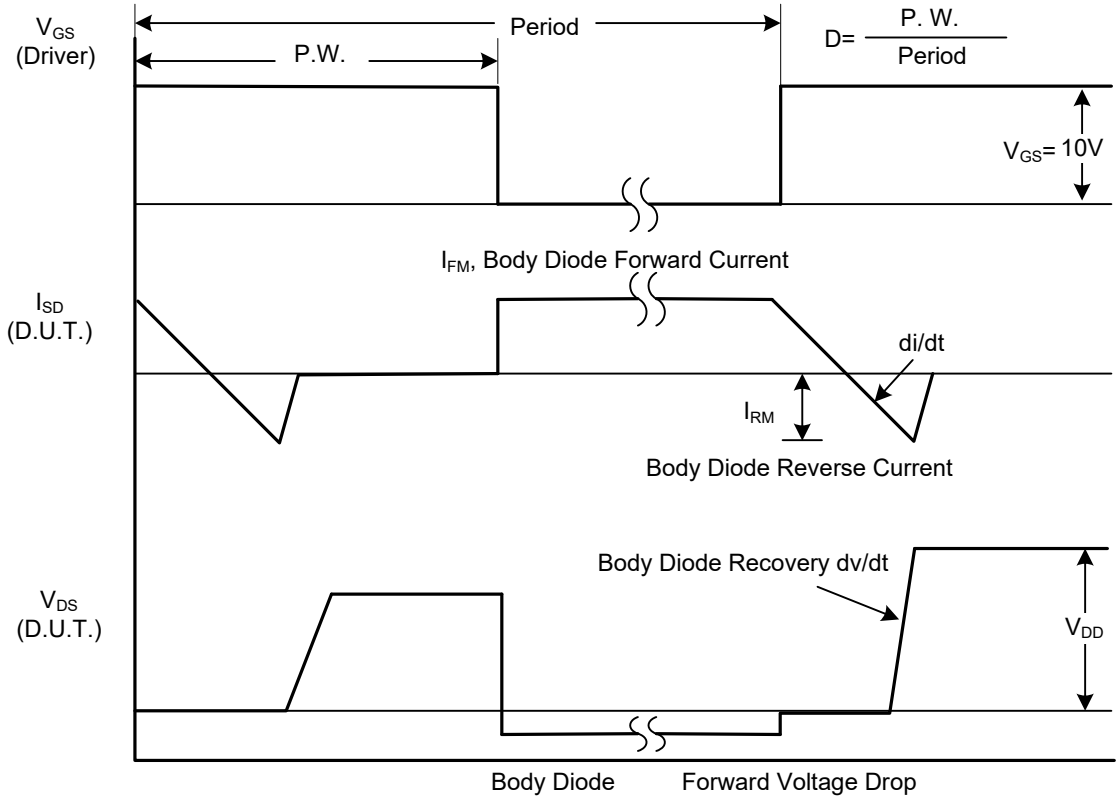
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	V_{GS}=0V, I_D=250μA	100			V
Drain-Source Leakage Current		I_{DSS}	V_{DS}=100V, V_{GS}=0V			1	μA
Gate-Source Leakage Current	Forward	I_{GSS}	V_{GS}=+20V, V_{DS}=0V			+100	nA
	Reverse		V_{GS}=-20V, V_{DS}=0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=250μA	1.0		3.0	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS}=10V, I_D=7.5A			90	mΩ
			V_{GS}=4.5V, I_D=7.5A			100	mΩ
DYNAMIC PARAMETERS							
Input Capacitance		C_{ISS}	V_{GS}=0V, V_{DS}=25V, f=1.0MHz		751		pF
Output Capacitance		C_{OSS}			114		pF
Reverse Transfer Capacitance		C_{RSS}			17		pF
SWITCHING PARAMETERS							
Total Gate Charge		Q_G	V_{DS}=80V, V_{GS}=10V, I_D=15A (Note 1, 2)		25		nC
Gate to Source Charge		Q_{GS}			6		nC
Gate to Drain Charge		Q_{GD}			12		nC
Turn-ON Delay Time		$t_{D(ON)}$	V_{DD}=50V, V_{GS}=10V, I_D=15A, R_G=25Ω (Note 1, 2)		8		ns
Rise Time		t_R			17		ns
Turn-OFF Delay Time		$t_{D(OFF)}$			70		ns
Fall-Time		t_F			22		ns
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Continuous Drain-Source Diode Forward Current		I_S				15	A
Maximum Pulsed Drain-Source Diode Forward Current		I_{SM}				30	A
Diode Forward Voltage		V_{SD}	I_F=15A, V_{GS}=0V			1.4	V
Reverse Recovery Time		t_{rr}	I_S=15A, V_{GS}=0V, dI_F/dt = 100 A/μs		105		ns
Reverse Recovery Charge (Note 1)		Q_{rr}			260		nC

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.
2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

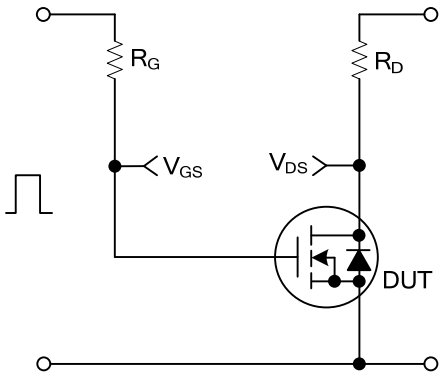


Peak Diode Recovery dv/dt Test Circuit

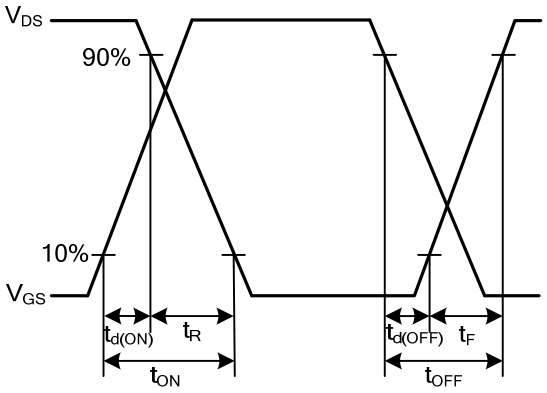


Peak Diode Recovery dv/dt Waveforms

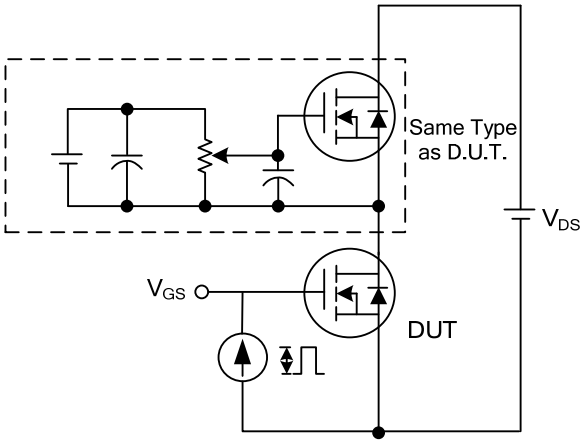
■ TEST CIRCUITS AND WAVEFORMS



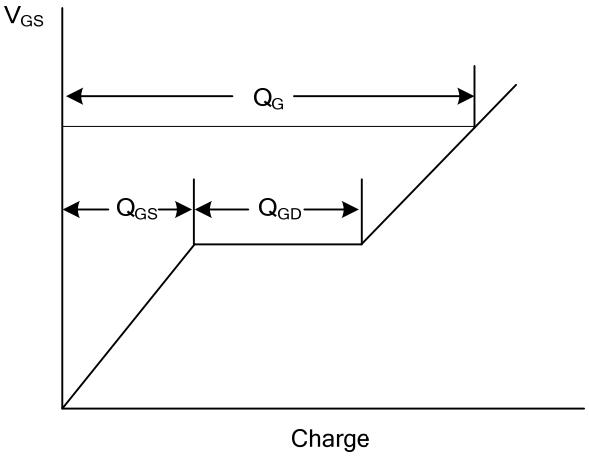
itching Test Circuit



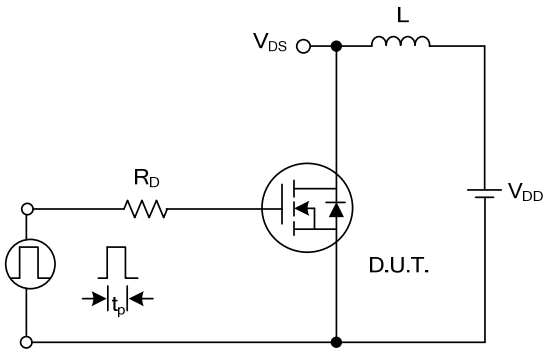
Switching Waveforms



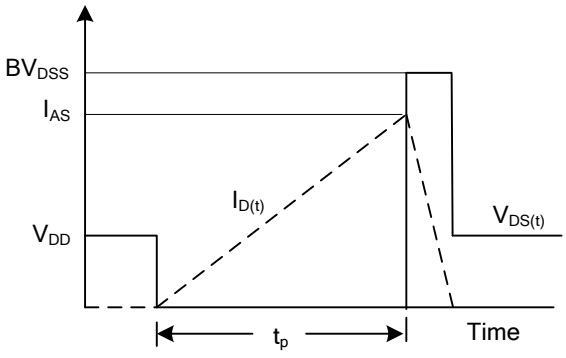
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms